Abstract

A method and an apparatus for the non-destructive detection of defects in the interior of semiconductor material (2) are disclosed. The semiconductor material (2) has a length (L), a cross-sectional area (Q), and a side surface (5) aligned with the length (L). An ultrasonic apparatus (10) is assigned to the semiconductor material (2). Furthermore a set-up (9) for generating a relative motion between the ultrasonic apparatus (10) and along the length (L) of the side surface (5) of the semiconductor material (2) is provided.

Figure 1